

# FDP18N50 / FDPF18N50 / FDPF18N50T N-Channel UniFET<sup>TM</sup> MOSFET

500 V, 18 A, 265 m $\Omega$ 

### Features

- +  $R_{DS(on)}$  = 220 m $\Omega$  (Typ.) @  $V_{GS}$  = 10 V, I<sub>D</sub> = 9 A
- Low Gate Charge (Typ. 45 nC)
- Low C<sub>rss</sub> (Typ. 25 pF)
- 100% Avalanche Tested

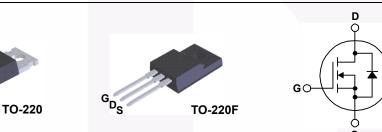
### Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

## Description

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

November 2013



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FDP18N50 FDPF18N50 FDPF18N50		Unit	
V <sub>DSS</sub>	Drain-Source Voltage		5	500		
ID	Drain Current	- Continuous ( $T_C = 25^{\circ}C$ ) - Continuous ( $T_C = 100^{\circ}C$ )	18 10.8	18 * 10.8 *	A A	
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	72	72 *	А	
V <sub>GSS</sub>	Gate-Source voltage		±	±30		
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		g	945		
I <sub>AR</sub>	Avalanche Current	(Note 1)		18		
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)		2	23.5		
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4	4.5		
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate Above 25°C	235 1.88	38.5 0.3	W W/∘C	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150		°C	
Τ <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300		°C	

\* Drain current limited by maximum junction temperature

### **Thermal Characteristics**

Symbol	Parameter	FDP18N50	FDPF18N50 / FDPF18N50T	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.53	3.3	°C/W
$R_{\thetaJA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W

Package	Marking	and	Orderina	Information
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Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDP18N50	FDP18N50	TO-220	Tube	N/A	N/A	50 units
FDPF18N50	FDPF18N50	TO-220F	Tube	N/A	N/A	50 units
FDPF18N50T	FDPF18N50T	TO-220F	Tube	N/A	N/A	50 units

## **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics				1 1	
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 V, I_{D} = 250 \mu A$	500			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 µA, Referenced to 25°C		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 500 V, V_{GS} = 0 V$ $V_{DS} = 400 V, T_{C} = 125^{\circ}C$			1 10	μΑ μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 9 A		0.220	0.265	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 9 A		25		S
Dynamic C	Characteristics				1 1	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		2200	2860	pF
C <sub>oss</sub>	Output Capacitance			330	430	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			25	40	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD}$ = 250 V, I <sub>D</sub> = 18 A, $V_{GS}$ = 10 V, R <sub>G</sub> = 25 $\Omega$ (Note 4)		55	120	ns
t <sub>r</sub>	Turn-On Rise Time			165	340	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			95	200	ns
t <sub>f</sub>	Turn-Off Fall Time			90	190	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 400 V, I <sub>D</sub> = 18 A,		45	60	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		12.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		19		nC
Drain-Sou	rce Diode Characteristics and Maximur	n Ratings				
I <sub>S</sub> Maximum Continuous Drain-Source Diode Forward Current					18	А
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				72	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 18 A,		500		ns
Q <sub>rr</sub>	Reverse Recovery Charge	_dI <sub>F</sub> /dt =100 A/μs		5.4		μC

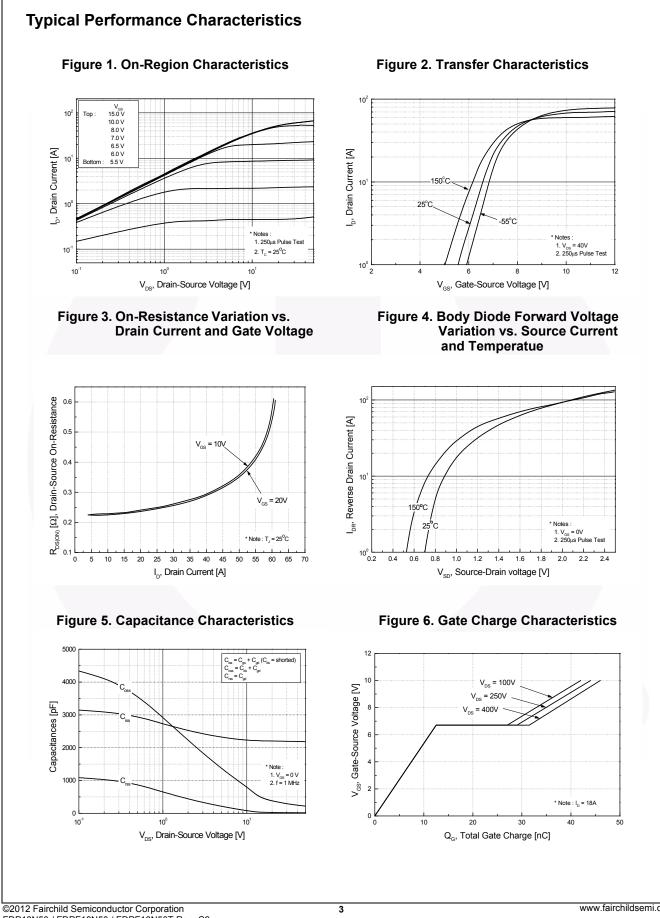
#### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.

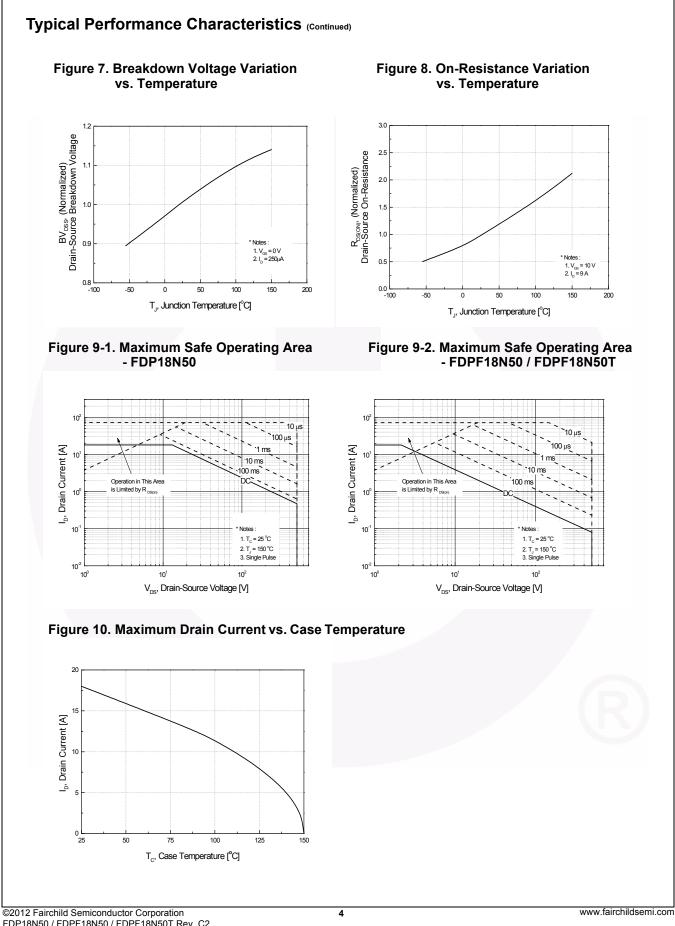
2. L = 5.2 mH, I<sub>AS</sub> = 18 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C.

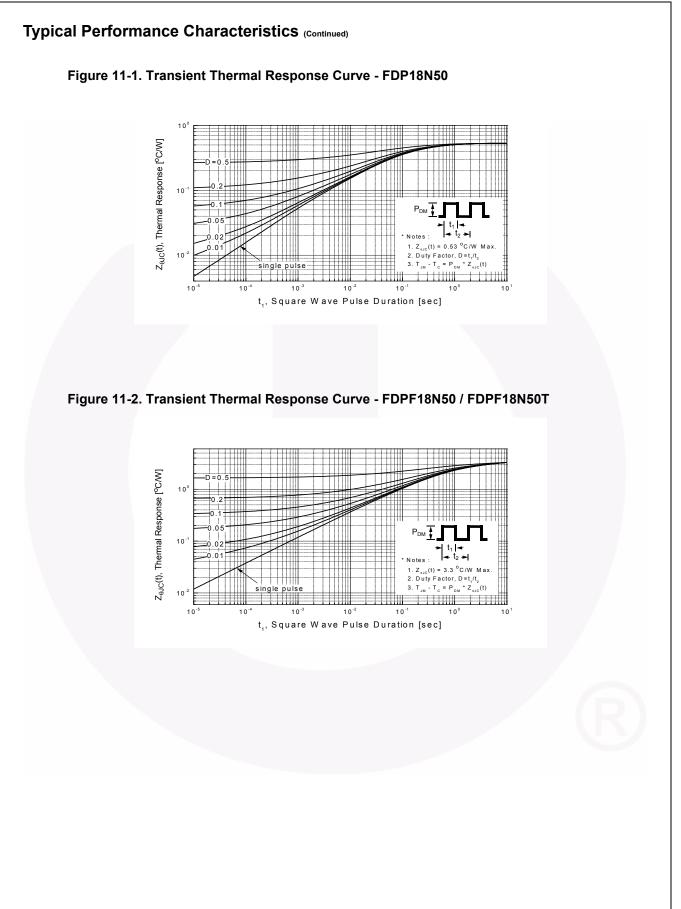
3. I\_{SD}  $\leq$  18 A, di/dt  $\leq$  200 A/µs, V\_{DD}  $\leq$  BV\_{DSS}, starting T\_J = 25°C.

4. Essentially independent of operating temperature typical characteristics.

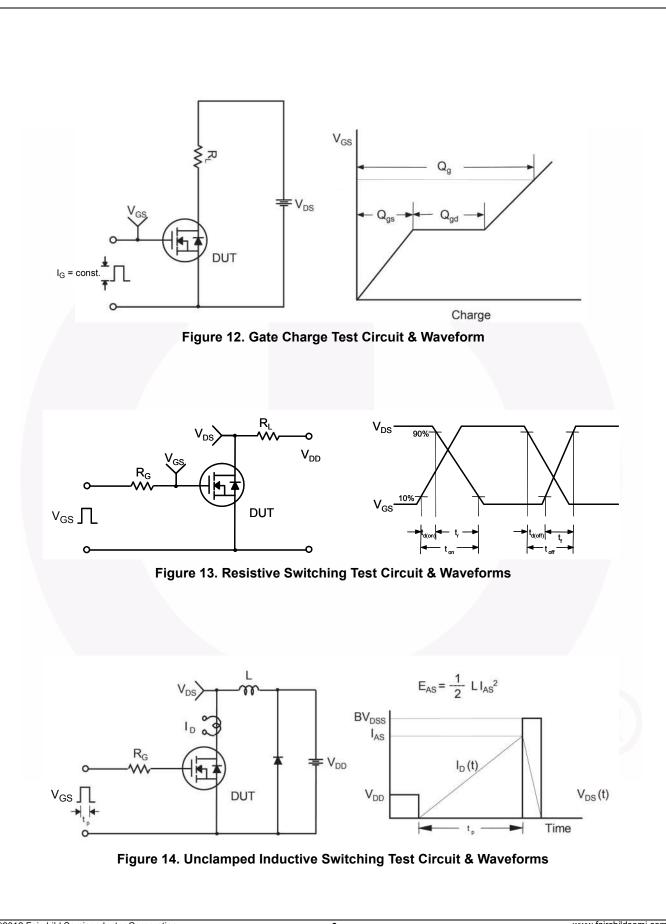


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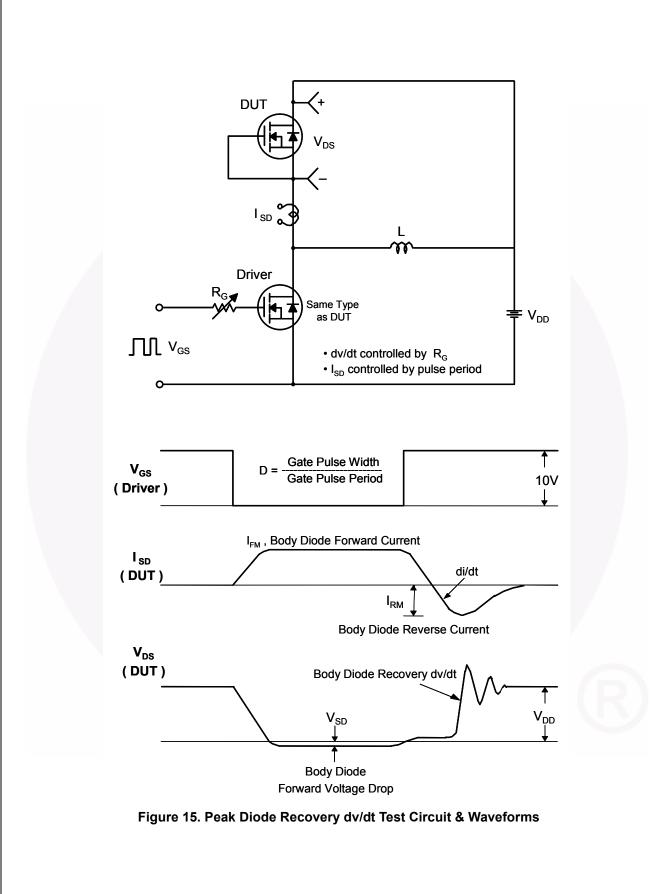


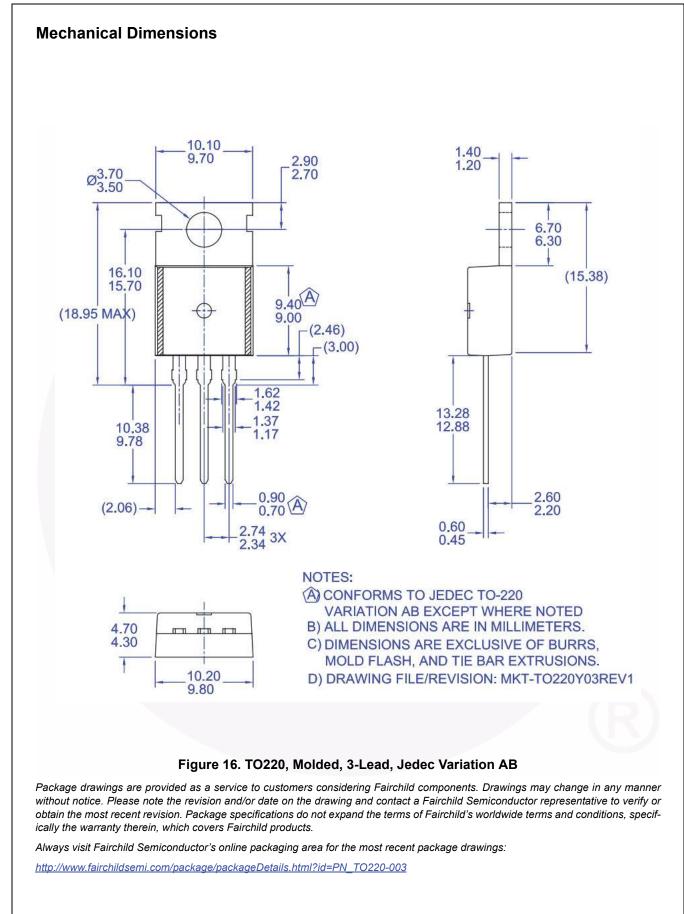


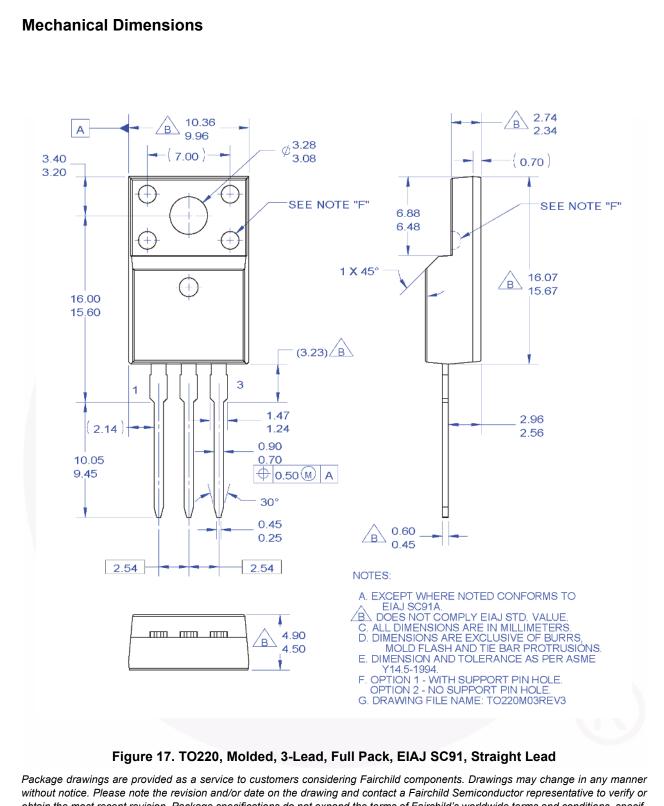
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